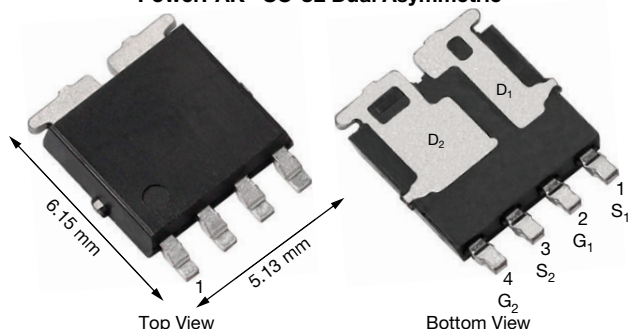


Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFETs

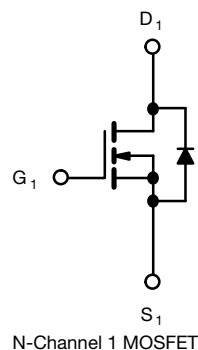
PowerPAK® SO-8L Dual Asymmetric


FEATURES

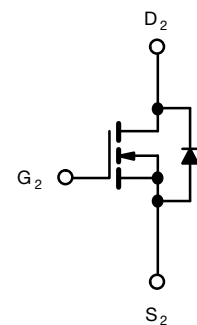
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V _{DS} (V)	60	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0355	0.0155
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.0480	0.0200
I _D (A)	15	40
Configuration	Dual N	
Package	PowerPAK SO-8L Dual Asymmetric	



N-Channel 1 MOSFET



N-Channel 2 MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-source voltage		V _{DS}	60	60	V
Gate-source voltage		V _{GS}	± 20		
Continuous drain current	T _C = 25 °C	I _D	15 ^a	40	A
	T _C = 125 °C		11	23	
Continuous source current (diode conduction)		I _S	15 ^a	44	
Pulsed drain current ^b		I _{DM}	30	70	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	12	20	
Single pulse avalanche energy		E _{AS}	7.2	20	mJ
Maximum power dissipation ^b	T _C = 25 °C	P _D	27	48	W
	T _C = 125 °C		9	16	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175		°C
Soldering recommendations (peak temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT	
Junction-to-ambient	R _{thJA}	85	85	°C/W	
Junction-to-case (drain)	R _{thJC}	5.5	3.1		

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT	
Static									
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		N-Ch 1	60	-	-	V	
		V _{GS} = 0 V, I _D = 250 μA		N-Ch 2	60	-	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 1	1.5	2.0	2.5	V	
		V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 2	1.5	2.0	2.5		
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		N-Ch 1	-	-	± 100	nA	
				N-Ch 2	-	-	± 100		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	N-Ch 1	-	-	1	μA	
		V _{GS} = 0 V	V _{DS} = 60 V	N-Ch 2	-	-	1		
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	N-Ch 1	-	-	50		
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	N-Ch 2	-	-	50		
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	N-Ch 1	-	-	250		
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	N-Ch 2	-	-	250		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 1	10	-	-	A	
		V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 2	20	-	-		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 2 A	N-Ch 1	-	0.0295	0.0355	Ω	
		V _{GS} = 10 V	I _D = 5 A	N-Ch 2	-	0.0126	0.0155		
		V _{GS} = 10 V	I _D = 2 A, T _J = 125 °C	N-Ch 1	-	-	0.0563		
		V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	N-Ch 2	-	-	0.0253		
		V _{GS} = 10 V	I _D = 2 A, T _J = 175 °C	N-Ch 1	-	-	0.0700		
		V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	N-Ch 2	-	-	0.0311		
		V _{GS} = 4.5 V	I _D = 1 A	N-Ch 1	-	0.0400	0.0480		
		V _{GS} = 4.5 V	I _D = 3 A	N-Ch 2	-	0.0165	0.0200		
Dynamic ^b									
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	410	550	pF	
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	967	1260		
Output capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	212	280	pF	
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	436	570		
Reverse transfer capacitance	C _{rss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	15	20	pF	
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	18	25		
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 1 A	N-Ch 1	-	6.5	10	nC	
		V _{GS} = 10 V	V _{DS} = 30 V, I _D = 2 A	N-Ch 2	-	14.5	23		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 1 A	N-Ch 1	-	1.4	-	nC	
		V _{GS} = 10 V	V _{DS} = 30 V, I _D = 2 A	N-Ch 2	-	2.7	-		
Gate-drain charge ^c	Q _{gd}	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 1 A	N-Ch 1	-	0.9	-	nC	
		V _{GS} = 10 V	V _{DS} = 30 V, I _D = 2 A	N-Ch 2	-	2.1	-		
Gate resistance	R _g	f = 1 MHz			N-Ch 1	0.7	1.47	2.2	Ω
					N-Ch 2	0.3	0.62	0.95	

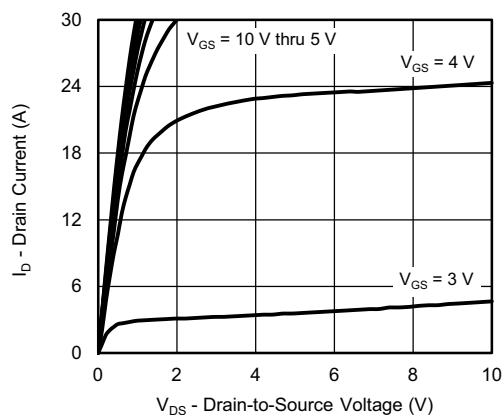
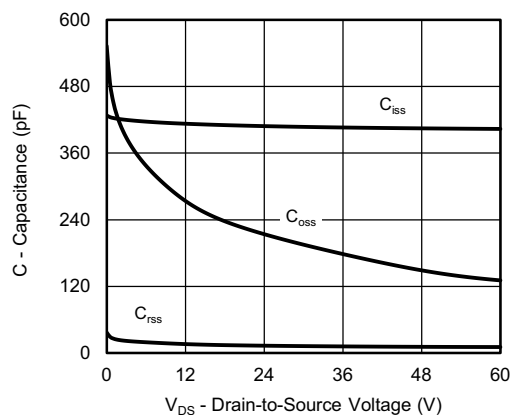
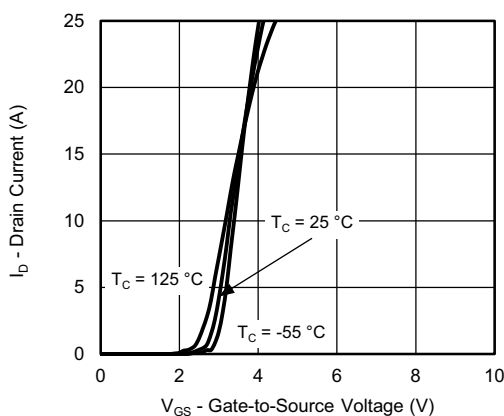
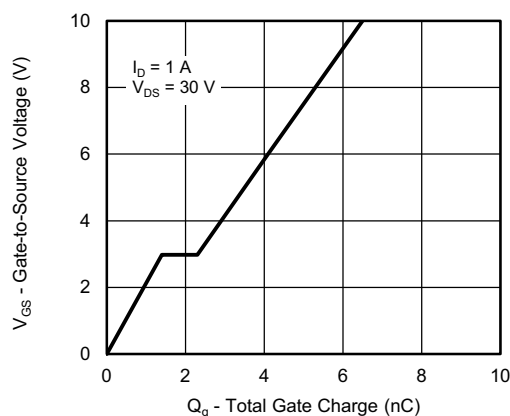
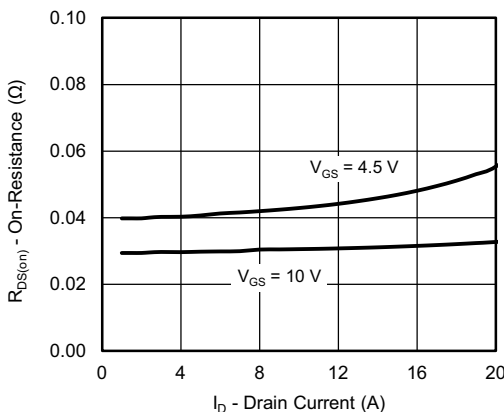
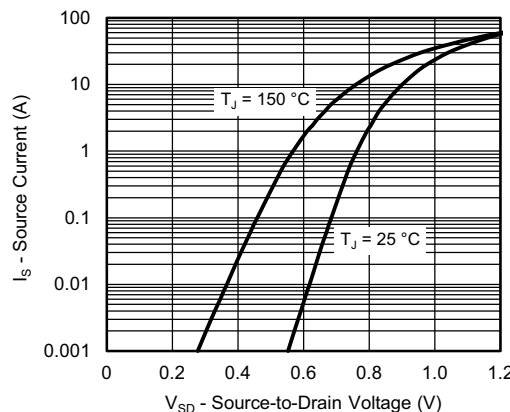


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Dynamic ^b							
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	9	15	ns
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	13	20	
Rise time ^c	t _r	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	3	5	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	3	5	
Turn-off delay time ^c	t _{d(off)}	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	15	25	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	23	35	
Fall time ^c	t _f	V _{DD} = 30 V, R _L = 30 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	10	15	
		V _{DD} = 30 V, R _L = 15 Ω, I _D ≅ 2 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	10	15	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}		N-Ch 1	-	-	30	A
			N-Ch 2	-	-	70	
Forward voltage	V _{SD}	I _F = 2 A, V _{GS} = 0 V	N-Ch 1	-	0.81	1.2	V
		I _F = 5 A, V _{GS} = 0 V	N-Ch 2	-	0.80	1.2	
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	24	50	ns
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	36	75	
Body diode reverse recovery charge	Q _{rr}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	17	35	nC
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	30	60	
Reverse recovery fall time	t _a	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	12	-	ns
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	19	-	
Reverse recovery rise time	t _b	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	12	-	
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	17	-	
Body diode peak reverse recovery current	I _{RM(REC)}	I _F = 2 A, di/dt = 100 A/μs	N-Ch 1	-	-1.3	-	A
		I _F = 3 A, di/dt = 100 A/μs	N-Ch 2	-	-1.6	-	

Notes

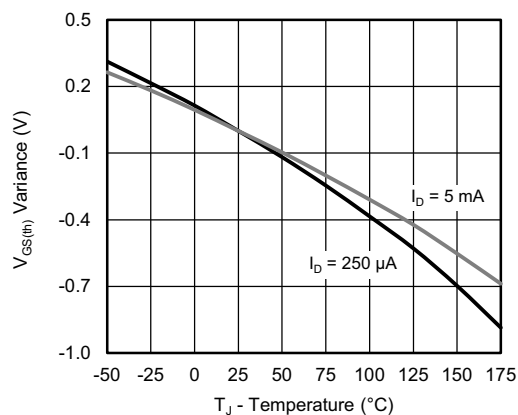
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

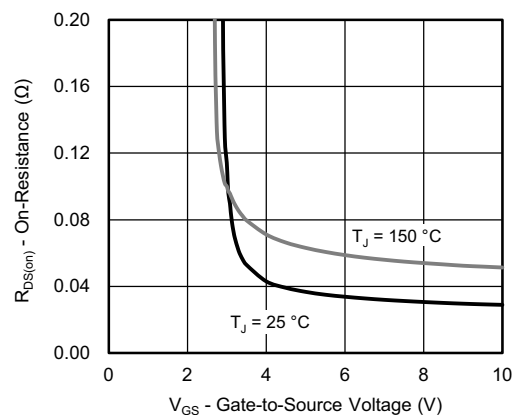
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Capacitance

Transfer Characteristics

Gate Charge

On-Resistance vs. Drain Current

Source Drain Diode Forward Voltage



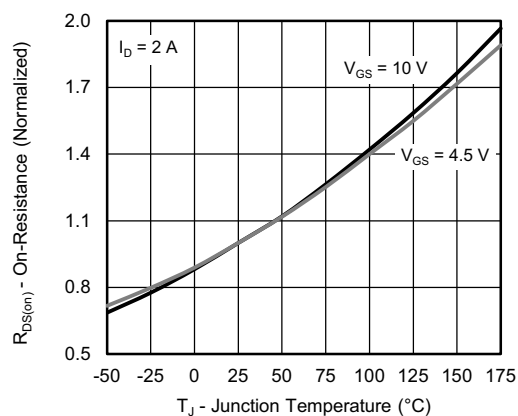
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



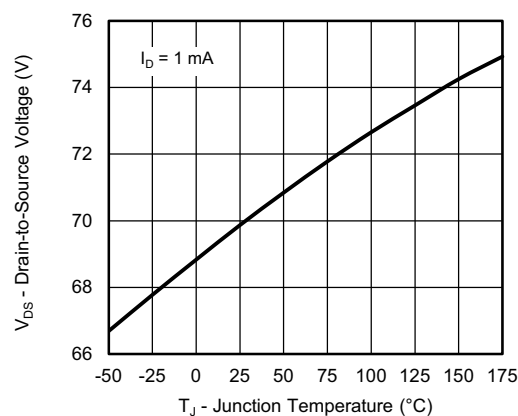
Threshold Voltage



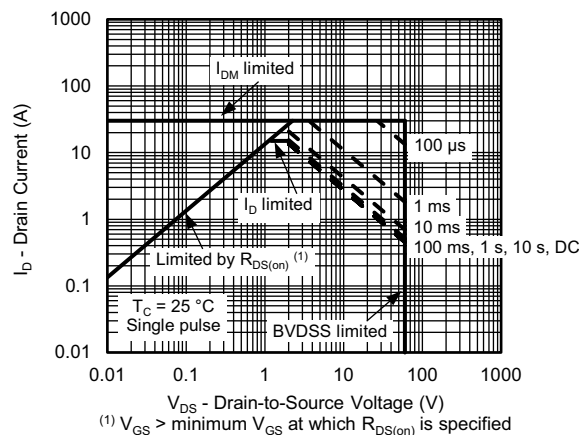
On-Resistance vs. Gate-to-Source Voltage



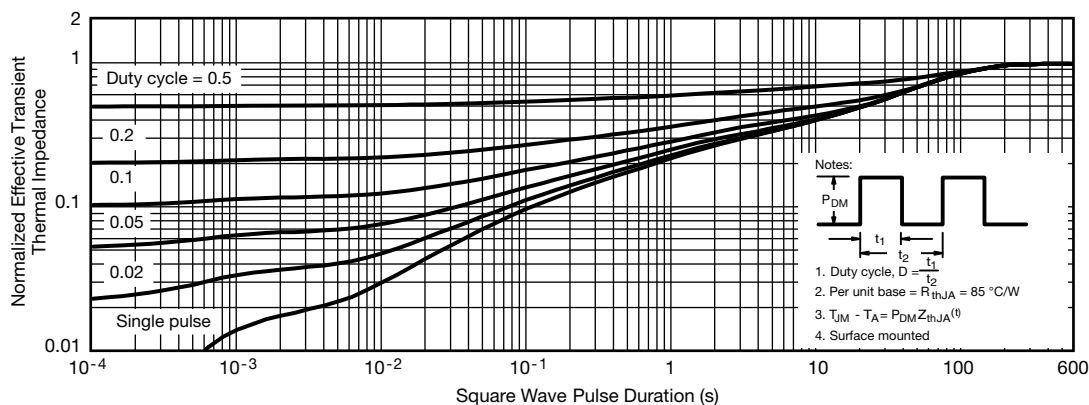
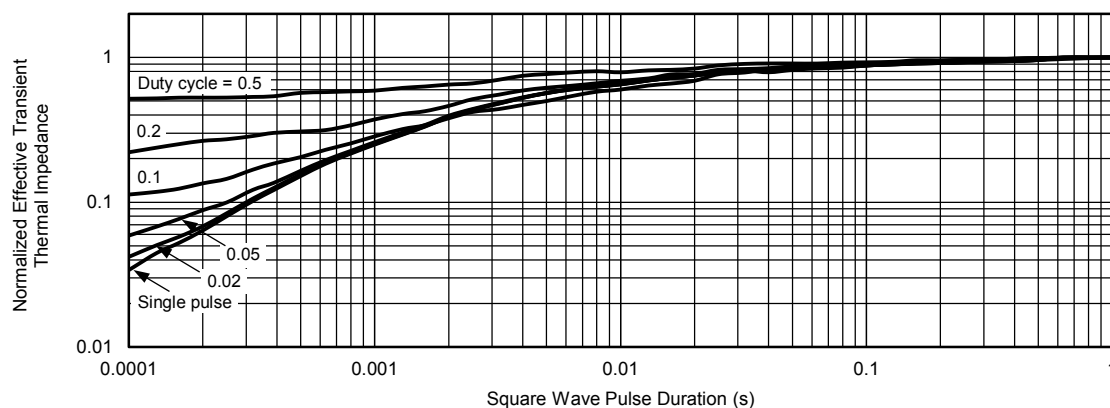
On-Resistance vs. Junction Temperature



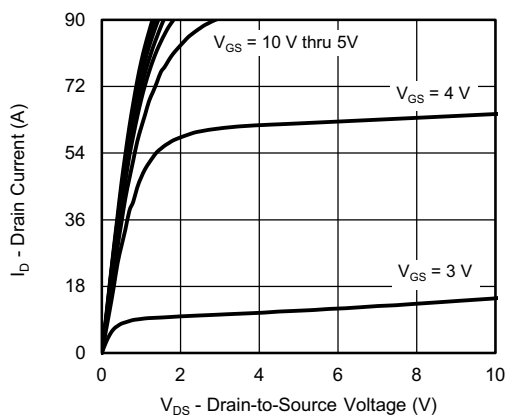
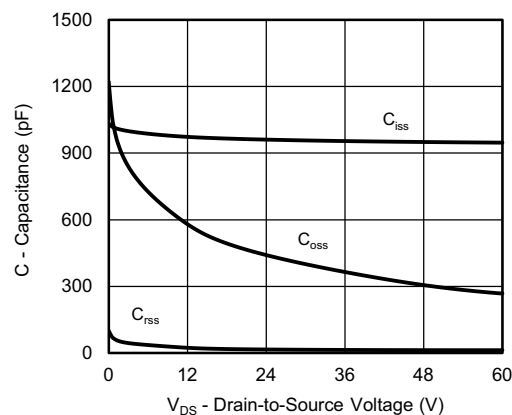
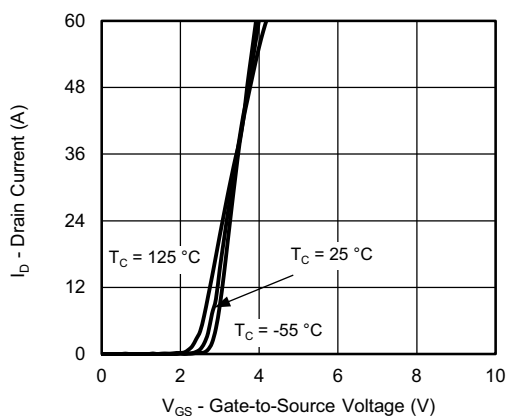
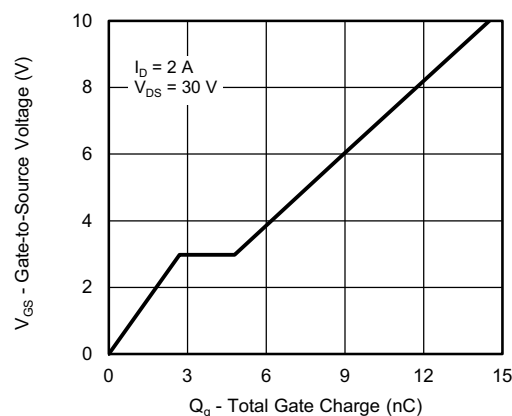
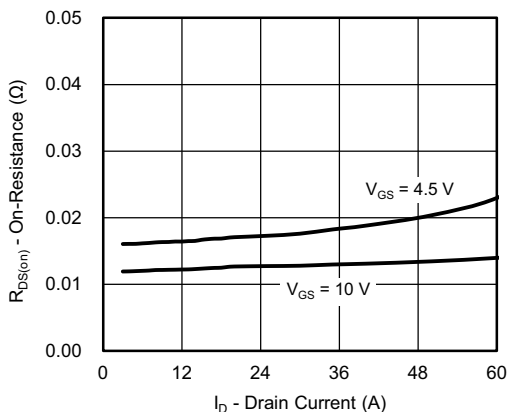
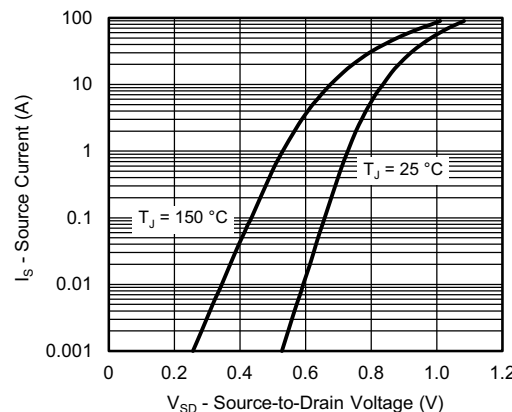
Drain Source Breakdown vs. Junction Temperature

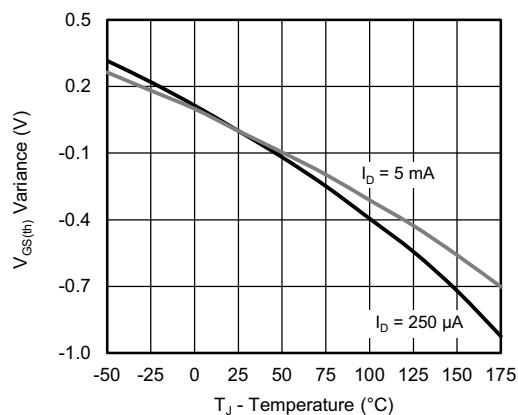
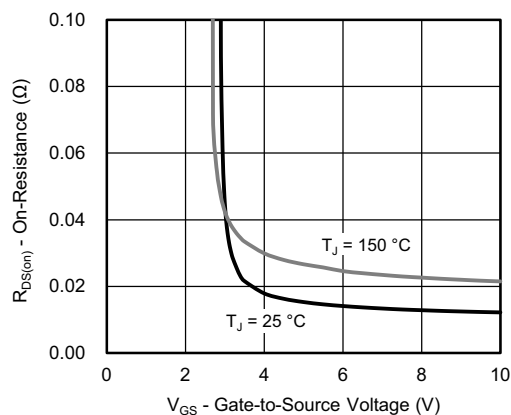
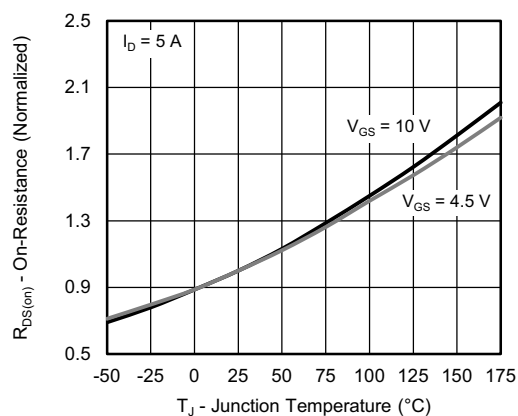
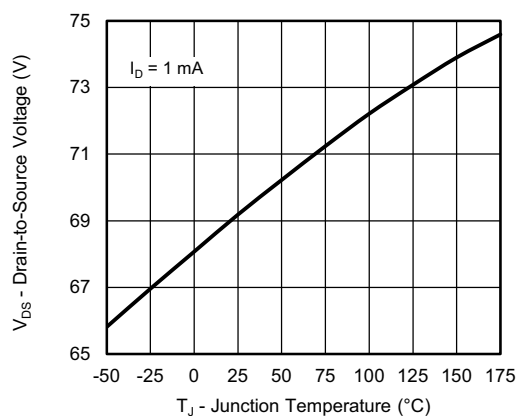
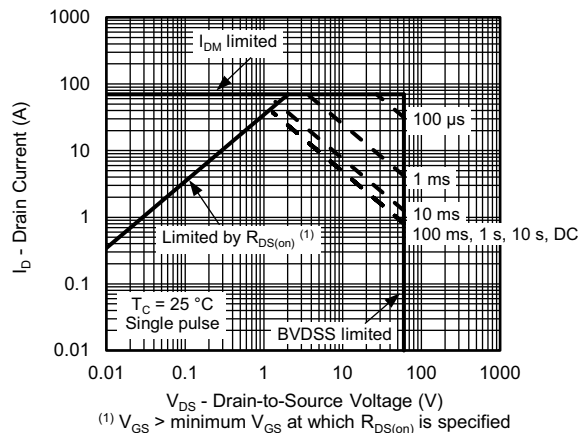


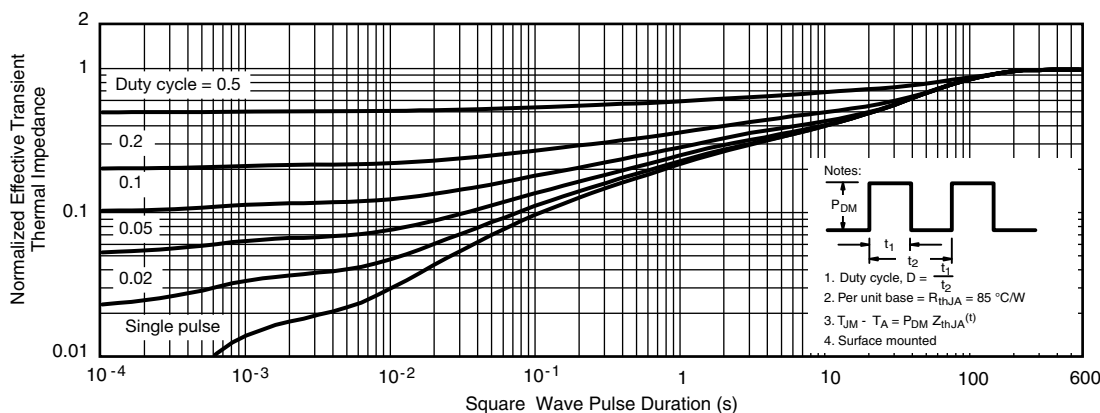
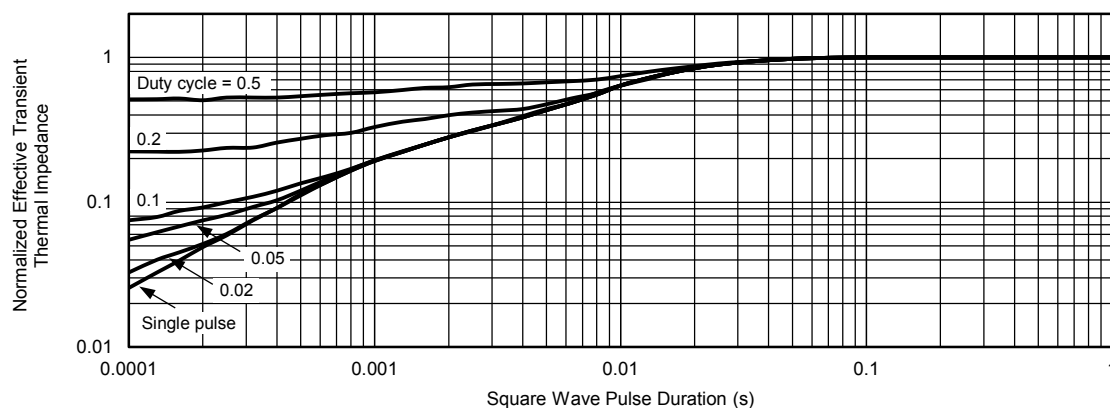
Safe Operating Area

N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Capacitance

Transfer Characteristics

Gate Charge

On-Resistance vs. Drain Current

Source Drain Diode Forward Voltage

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

On-Resistance vs. Junction Temperature

Drain Source Breakdown vs. Junction Temperature

Safe Operating Area

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

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